

ADS9226 16 位双通道、低延迟、同步采样 SAR ADC

1 特性

- 高分辨率、高吞吐量：
 - 16 位，2.048MSPS
- 低延迟快速响应时间：488ns
- 两个同步采样通道
- 单极伪差分输入
- 出色的直流和交流性能：
 - 16 位，无丢码
 - $\pm 2.75\text{LSB}$ 最大 INL
 - 90.8dB SNR, -100dB THD
- 宽模拟电源电压范围：4V 至 5.5V
- 集成式基准缓冲器
- SPI 兼容串行接口
- 工作温度范围：-40°C 至 +125°C
- 小尺寸：5mm × 5mm VQFN

2 应用

- [伺服驱动器位置反馈](#)
- [伺服驱动器功率级模块](#)
- [电信光模块](#)
- [电能质量分析仪](#)
- [直流/交流电源，电子负载](#)

3 说明

ADS9226 是一款 16 位双通道同步采样模数转换器 (ADC)，具有集成式基准缓冲器。该器件可由 5V 单电源供电运行，支持单极和伪差分模拟输入信号，具有出色的直流和交流规格。

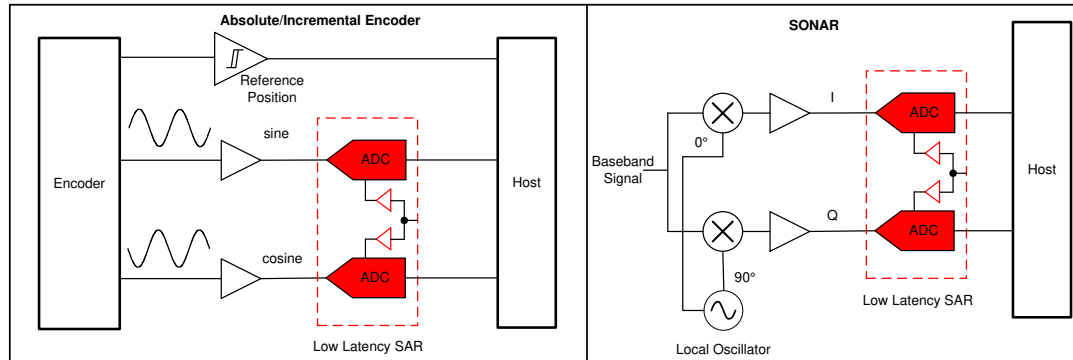
该器件支持 SPI 兼容串行 (增强型 SPI) 接口，因此易于与多种微控制器、数字信号处理器 (DSP) 和现场可编程门阵列 (FPGA) 搭配使用。

该器件采用节省空间的 5mm × 5mm VQFN 封装。ADS9226 的额定工作温度范围为 -40°C 至 +125°C。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
ADS9226	VQFN (32)	5.00mm x 5.00mm

- (1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。



典型应用图



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

DATE	REVISION	NOTES
July 2020	*	Initial release.

5 Pin Configuration and Functions

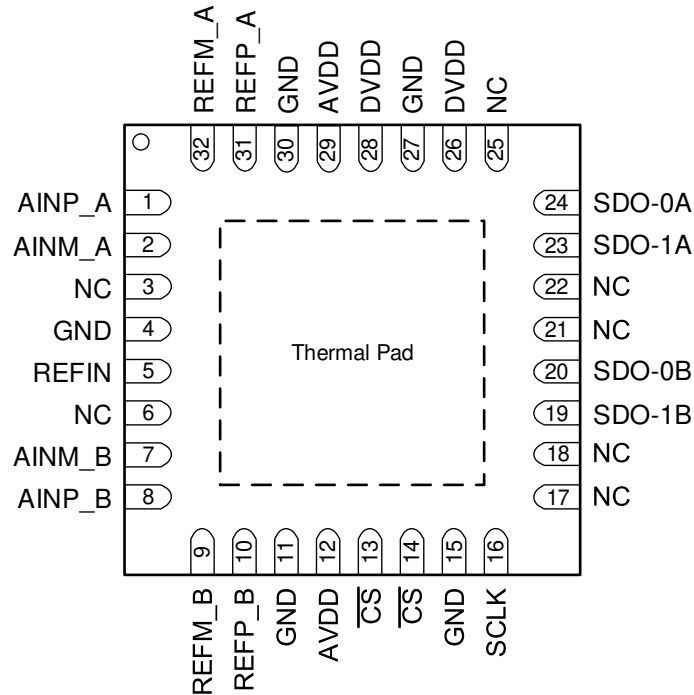


图 5-1. RHB Package, 5-mm × 5-mm, 32-Pin VQFN, Top View

Pin Functions

PIN		FUNCTION	DESCRIPTION
NAME	NO.		
AINM_A	2	Analog input	Negative analog input for channel A.
AINM_B	7	Analog input	Negative analog input for channel B.
AINP_A	1	Analog input	Positive analog input for channel A.
AINP_B	8	Analog input	Positive analog input for channel B.
AVDD	12, 29	Power supply	Analog power-supply pin. Short pins 12 and 29 together. Place a 1- μ F decoupling capacitor between pins 11 and 12. Place a 1- μ F decoupling capacitor between pins 29 and 30.
\overline{CS}	13, 14	Digital input	Chip-select input pin; active low. The device takes control of the data bus when \overline{CS} is low. The SDO-xy pins go to Hi-Z when \overline{CS} is high. Connect these pins together externally with a short trace.
DVDD	26, 28	Power supply	Interface power-supply pin. Place a 1- μ F decoupling capacitor between pins 27 and 26 and pins 27 and 28.
GND	4, 11, 15, 27, 30	Power supply	Device ground.
NC	3, 6, 17, 18, 21, 22, 25	No connection	No external connection.

PIN		FUNCTION	DESCRIPTION
NAME	NO.		
REFIN	5	Analog input	Reference voltage for the ADC.
REFM_A	32	Analog input	ADC_A negative reference input. Externally connect to the device GND.
REFM_B	9	Analog input	ADC_B negative reference input. Externally connect to the device GND.
REFP_A	31	Analog output	Positive output of reference buffer A. ADC_A positive reference input. Place a 10- μ F decoupling capacitor between pins 31 and 32.
REFP_B	10	Analog output	Positive output of reference buffer B. ADC_B positive reference input. Place a 10- μ F decoupling capacitor between pins 9 and 10.
SCLK	16	Digital input	Clock input pin for the serial interface.
SDO-0A	24	Digital output	Data output 0 for channel A.
SDO-0B	20	Digital output	Data output 0 for channel B.
SDO-1A	23	Digital output	Data output 1 for channel A.
SDO-1B	19	Digital output	Data output 1 for channel B.
Thermal pad		Supply	Exposed thermal pad. TI recommends connecting this pin to the printed circuit board (PCB) ground.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
AVDD to GND	- 0.3	6	V
DVDD to GND	- 0.3	6	V
Digital input pins	GND - 0.3	DVDD + 0.3	V
Digital output pins	GND - 0.3	DVDD + 0.3	V
AINP_A, AINP_B to GND, AINM_A, AINM_B to GND	- 0.3	AVDD + 0.3	V
REFM_A, REFM_B	GND - 0.1	GND + 0.1	V
REFP_A, REFP_B to GND	GND - 0.3	AVDD + 0.3	V
Reference input voltage	REFIN to GND	AVDD + 0.3	V
Input or output current to any pin except power-supply pin	- 10	10	mA
Junction temperature, T _J		150	°C
Storage temperature, T _{stg}	- 65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins ⁽¹⁾	±2000
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLY					
AVDD		4	5	5.5	V
DVDD	Operating	1.65	3	5.5	V
	SCLK > 20 MHz	2.35	3	5.5	
EXTERNAL REFERENCE INPUT					
V _{REFIN}	External reference input voltage	1.4	AVDD/2	AVDD/1.75 - 0.2	V
ANALOG INPUTS					
FSR	Full-scale input range	- V _{REFIN}		V _{REFIN}	V
V _{INP_x}	Absolute input voltage AINP_x ⁽¹⁾	- 0.1		AVDD + 0.1	V
V _{INM_x}	Absolute input voltage AINM_x ⁽²⁾	V _{REFIN} - 0.1	V _{REFIN}	V _{REFIN} + 0.1	V
TEMPERATURE RANGE					
T _A	Ambient temperature	- 40	25	125	°C

- (1) AINP_x refers to AINP_A and AINP_B positive input pins for ADC_A and ADC_B respectively.
 (2) AINM_x refers to AINM_A and AINM_B positive input pins for ADC_A and ADC_B respectively.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		ADS9226	UNIT
		RHB (VQFN)	
		32 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	29	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	17.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	9.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	0.2	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	9.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	0.8	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at AVDD = 4 V to 5.5 V, DVDD = 3.3 V, V_{REFIN} = AVDD / 2 and maximum throughput (unless otherwise noted); minimum and maximum values at T_A = - 40°C to +125°C; typical values at T_A = 25°C and AVDD = 5 V

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
I _{IN}	Analog input leakage current			±1		µA
C _i	Input capacitance	Sample mode		16		pF
		Hold mode		1		
BW	Analog input bandwidth	- 3-dB input signal		52		MHz
		- 0.1-dB input signal		4.2		
DC ACCURACY						
	Resolution	No missing codes		16		bit
DNL	Differential nonlinearity		- 0.55	±0.25	0.55	LSB
INL	Integral nonlinearity		- 2.75	±1	2.75	LSB
E _O	Offset error		- 9	±2	9	LSB
	Offset error matching			±0.5		
$\Delta E_O / \Delta T$	Offset error temperature drift			1		ppm/°C
G _E	Gain error		- 0.027	±0.01	0.027	%FSR
	Gain error matching			0.2		
$\Delta G_E / \Delta T$	Gain drift			5		ppm/°C
	Transition noise	Mid code, PFS - 1000, NFS + 1000		0.675		LSB
AC ACCURACY						
SNR	Signal-to-noise ratio	f _{IN} = 2 kHz	88	90.8		dB
		f _{IN} = 100 kHz		90		
SINAD	Signal-to-noise plus distortion	f _{IN} = 2 kHz	87	90.5		dB
		f _{IN} = 100 kHz		89.6		
THD	Total harmonic distortion	f _{IN} = 2 kHz		- 100		dB
		f _{IN} = 100 kHz		- 95		
SFDR	Spurious-free dynamic range	f _{IN} = 2 kHz		105		dB
		f _{IN} = 100 kHz		100		
ISOXT	Channel to channel isolation	f _{IN_ADCA} = 15 kHz at 10% FSR f _{IN_ADCB} = 25 kHz at 100% FSR		- 115		dB

at AVDD = 4 V to 5.5 V, DVDD = 3.3 V, V_{REFIN} = AVDD / 2 and maximum throughput (unless otherwise noted); minimum and maximum values at T_A = - 40°C to +125°C; typical values at T_A = 25°C and AVDD = 5 V

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
INTERNAL REFERENCE BUFFER						
G _{REFBUF}	Reference buffer gain			1.75		V/V
	Reference buffer output offset (V _{REFP_x} - V _{REFIN}) ⁽¹⁾		- 1	0	1	mV
	Reference buffer output offset temperature drift			10		μV/C
	Reference buffer output mismatch (V _{REFP_A} - V _{REFP_B})		- 500	±50	500	μV
C _{REFP_x}	Reference buffer output capacitor	For specified performance, between each pair of REFP_x and REFM_x	7	10	27	μF
DIGITAL INPUTS						
V _{IH}	High-level input voltage	DVDD > 2.3 V	0.7 × DVDD		DVDD + 0.3	V
V _{IL}	Low-level input voltage		- 0.3		0.3 × DVDD	V
V _{IH}	High-level input voltage	DVDD ≤ 2.3 V	0.8 × DVDD		DVDD + 0.3	V
V _{IL}	Low-level input voltage		- 0.3		0.2 × DVDD	V
DIGITAL OUTPUTS						
V _{OH}	High-level output voltage	I _{OH} = 500-μA source	0.8 × DVDD		DVDD	V
V _{OL}	Low-level output voltage	I _{OH} = 500-μA sink	0		0.2 × DVDD	V
POWER SUPPLY						
I _{AVDD}	Analog supply current	AVDD = 5 V, f _{DATA} = 2.048 MSPS	16.5		20	mA
		AVDD = 5 V, no conversion	9			
PSRR	Power supply rejection ratio	100-mV _{p-p} ripple on AVDD, frequency < 100 kHz	70			dB

(1) REFP_x refers to the REFP_A and REFP_B reference pins for the ADC_A and ADC_B respectively.

6.6 Timing Requirements

at AVDD = 4 V to 5.5 V, DVDD = 2.35 V to 5.5 V and maximum throughput (unless otherwise noted); minimum and maximum values at $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$; typical values at $T_A = 25^{\circ}\text{C}$, AVDD = 5 V and DVDD = 3.3 V

		MIN	NOM	MAX	UNIT
CONVERSION CONTROL					
t_{Cycle}	Cycle time	488			ns
f_{Sample}	Sampling rate			2048	kSPS
t_{ACQ}	Acquisition time	$t_{\text{CYCLE}} - 160$			ns
$t_{\text{WH}_{\overline{\text{CS}}}}$	Pulse duration: $\overline{\text{CS}}$ high	15			ns
$t_{\text{WL}_{\overline{\text{CS}}}}$	Pulse duration: $\overline{\text{CS}}$ low	15			ns
SPI MODES					
f_{CLK}	Serial clock frequency			32.768	MHz
t_{CLK}	Serial clock time period	$1/f_{\text{CLK}}$			
$t_{\text{PH}_{\text{CLK}}}$	SCLK high time	0.45		0.55	t_{CLK}
$t_{\text{PL}_{\text{CLK}}}$	SCLK low time	0.45		0.55	t_{CLK}
$t_{\text{SU}_{\text{CSCK}}}$	Setup time: $\overline{\text{CS}}$ falling to first SCLK capture edge	14			ns
$t_{\text{HT}_{\text{CKCS}}}$	Delay time: last SCLK launch edge to $\overline{\text{CS}}$ rising	8			ns

6.7 Switching Characteristics

at AVDD = 4 V to 5.5 V, DVDD = 2.35 V to 5.5 V and maximum throughput (unless otherwise noted); minimum and maximum values at $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$; typical values at $T_A = 25^{\circ}\text{C}$, AVDD = 5 V and DVDD = 3.3 V

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
CONVERSION					
t_{CONV}	Conversion time			422	ns
SPI MODES					
$t_{\text{DEN}_{\text{CSDO}}}$	Delay time: $\overline{\text{CS}}$ falling to data valid on SDO-x			14	ns
$t_{\text{DZ}_{\text{CSDO}}}$	Delay time: $\overline{\text{CS}}$ rising edge to SDO-x tristate			13	ns
$t_{\text{D}_{\text{CKDO}}}$	Delay time: SCLK launch edge to next data valid on SDO-x			16	ns

6.8 Timing Diagrams

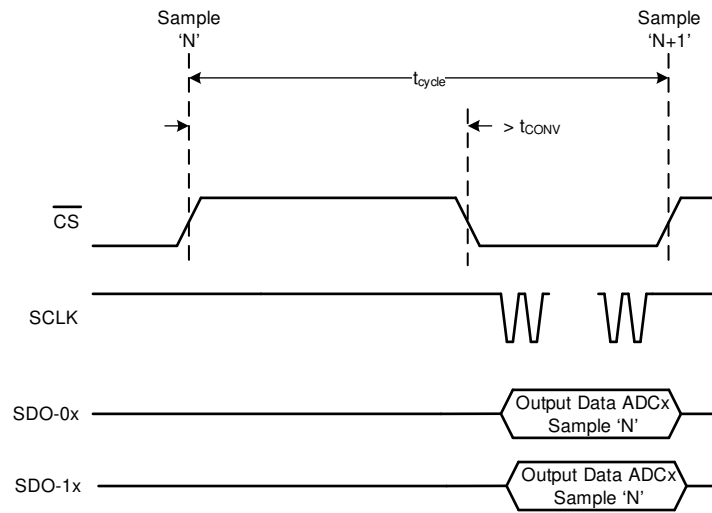


图 6-1. Conversion Control Latency-0 Data Capture

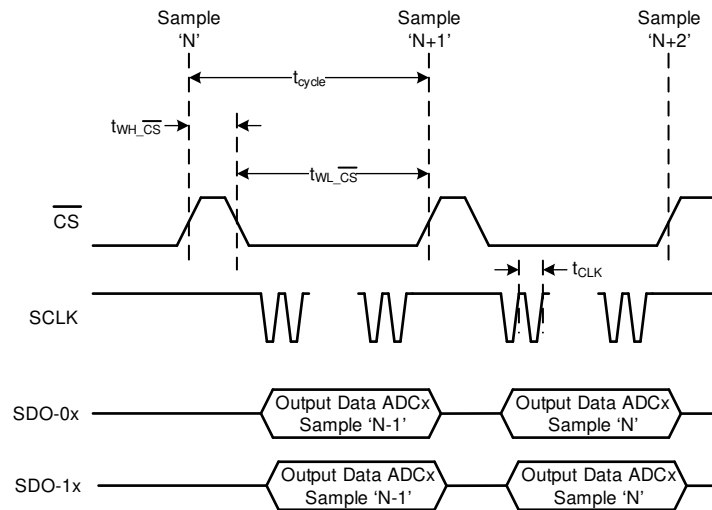


图 6-2. Conversion Control Latency-1 Data Capture

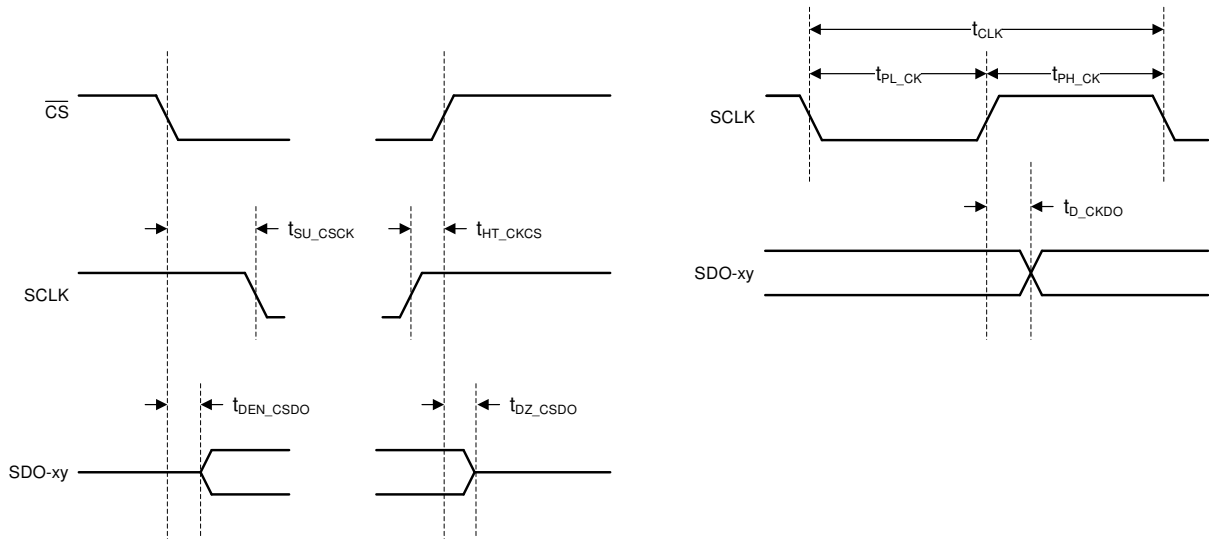
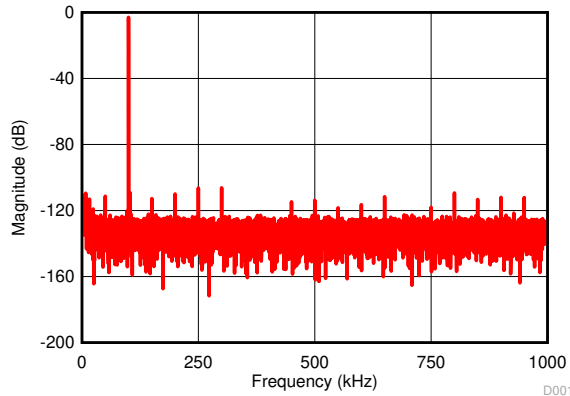


图 6-3. SPI-Compatible Serial Interface Timing

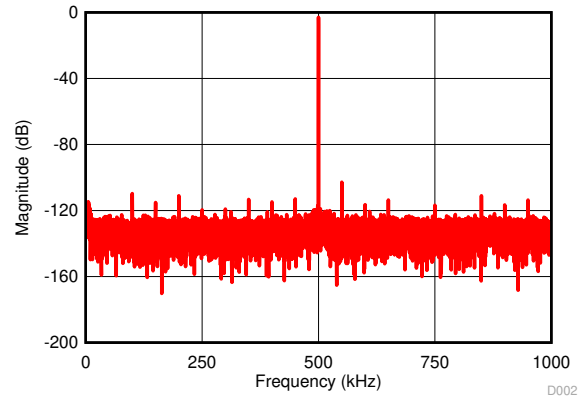
6.9 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $AVDD = 5\text{ V}$, $DVDD = 3.3\text{ V}$, $V_{REFIN} = 2.5\text{ V}$, and $f_{\text{Sample}} = 2.048\text{ MSPS}$ (unless otherwise noted)



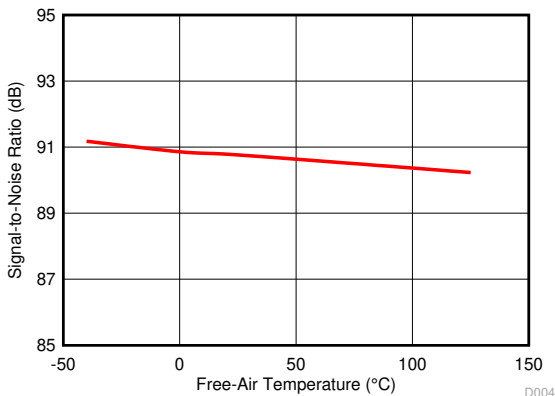
$f_{\text{IN}} = 100\text{ kHz}$, SNR = 90.1 dB, THD = -99.3 dB

图 6-4. Typical FFT at $f_{\text{IN}} = 100\text{ kHz}$



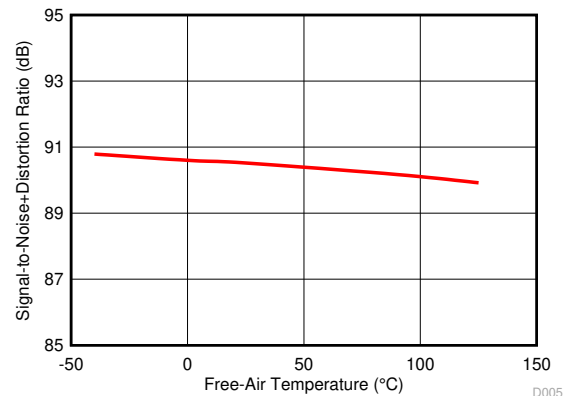
$f_{\text{IN}} = 500\text{ kHz}$, SNR = 90 dB, THD = -90.9 dB

图 6-5. Typical FFT at $f_{\text{IN}} = 500\text{ kHz}$



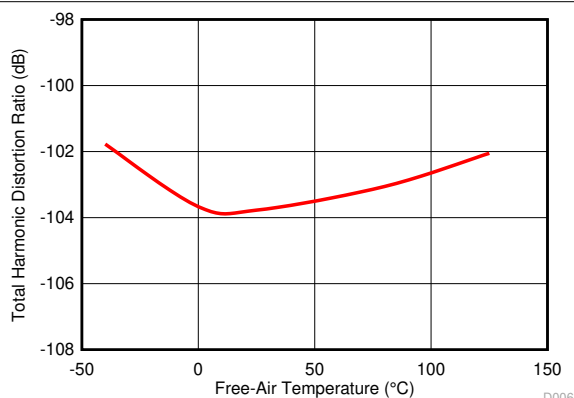
$f_{\text{IN}} = 2\text{ kHz}$

图 6-6. SNR vs Free-Air Temperature



$f_{\text{IN}} = 2\text{ kHz}$

图 6-7. SINAD vs Free-Air Temperature



$f_{\text{IN}} = 2\text{ kHz}$

图 6-8. THD vs Free-Air Temperature

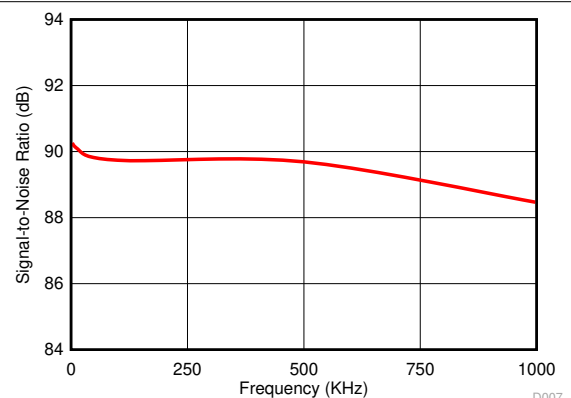


图 6-9. SNR vs Input Frequency

6.9 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $AVDD = 5\text{ V}$, $DVDD = 3.3\text{ V}$, $V_{REFIN} = 2.5\text{ V}$, and $f_{\text{Sample}} = 2.048\text{ MSPS}$ (unless otherwise noted)

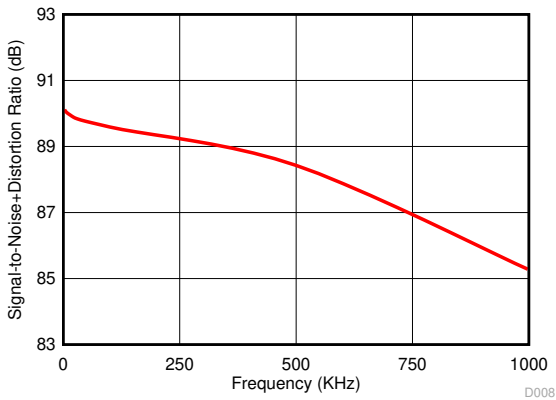


图 6-10. SINAD vs Input Frequency

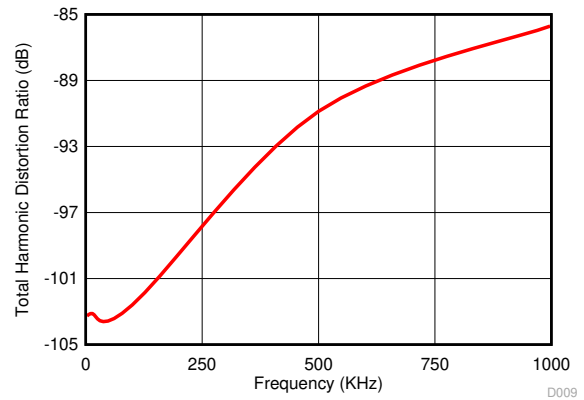
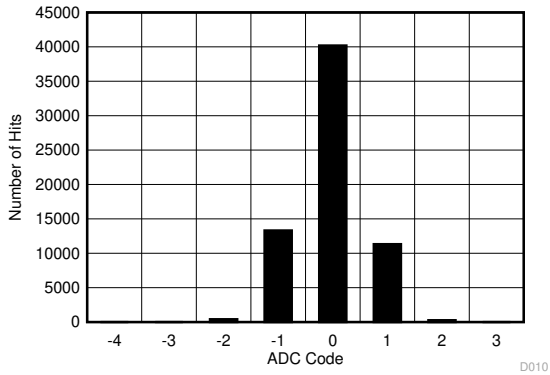


图 6-11. THD vs Input Frequency



Standard deviation = 0.65 LSB

图 6-12. DC Input Histogram

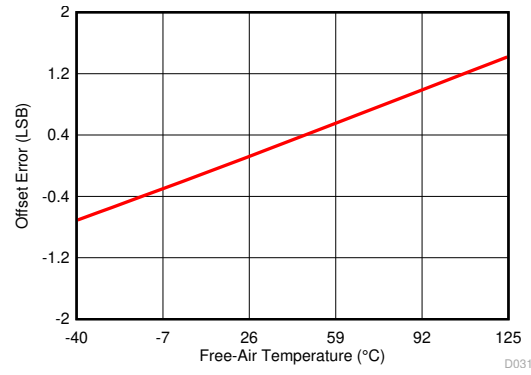


图 6-13. Offset Error vs Free-Air Temperature

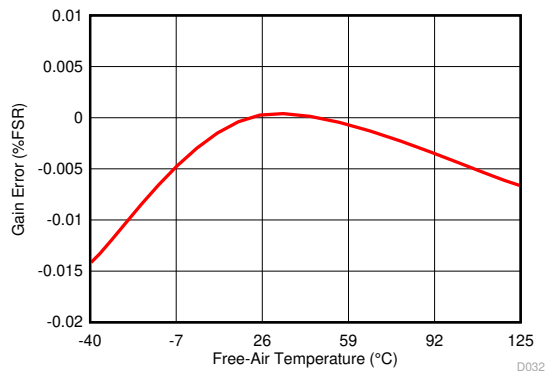


图 6-14. Gain Error vs Free-Air Temperature

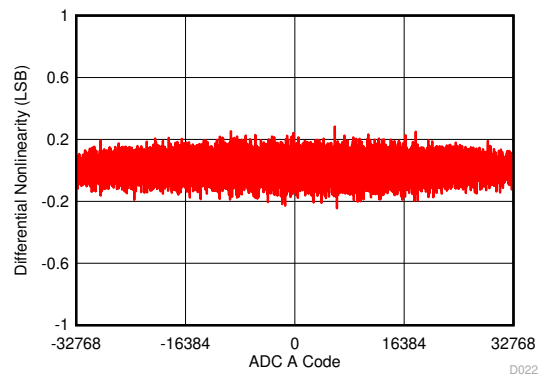


图 6-15. Typical DNL ADC A

6.9 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $AVDD = 5\text{ V}$, $DVDD = 3.3\text{ V}$, $V_{REFIN} = 2.5\text{ V}$, and $f_{\text{Sample}} = 2.048\text{ MSPS}$ (unless otherwise noted)

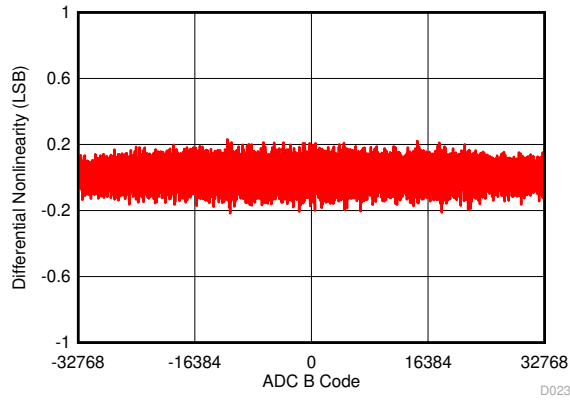


图 6-16. Typical DNL ADC B

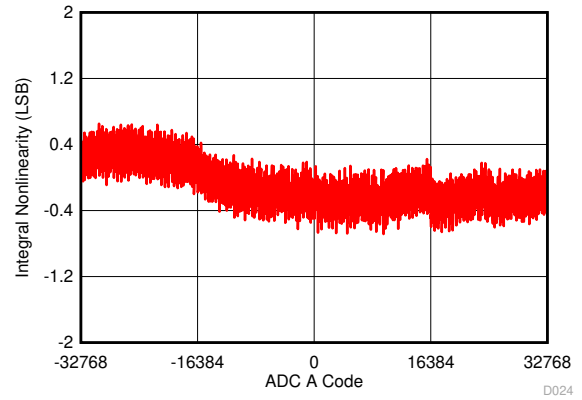


图 6-17. Typical INL ADC A

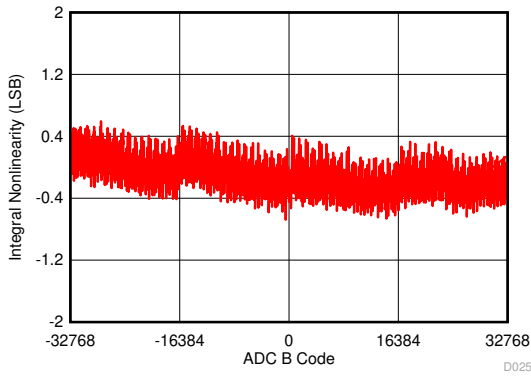


图 6-18. Typical INL ADC B

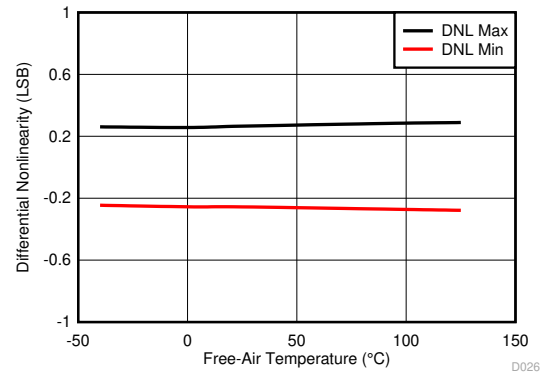


图 6-19. DNL vs Free-Air Temperature

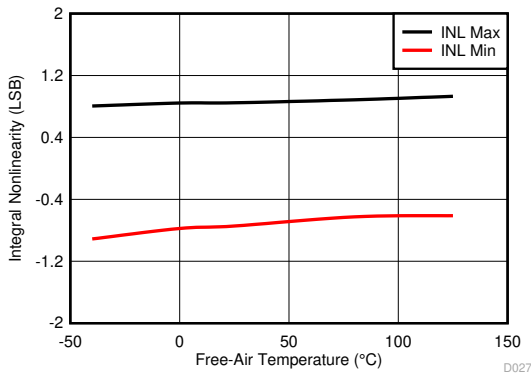


图 6-20. INL vs Free-Air Temperature

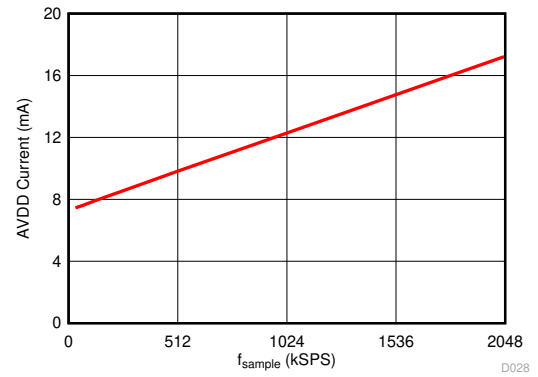
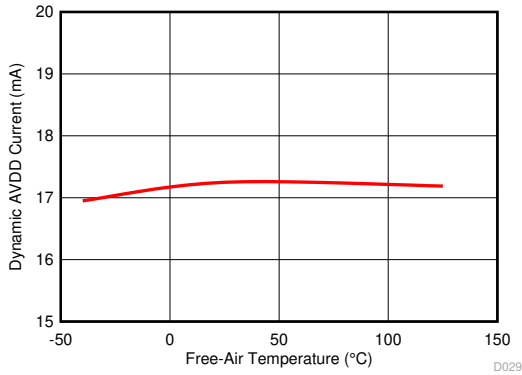


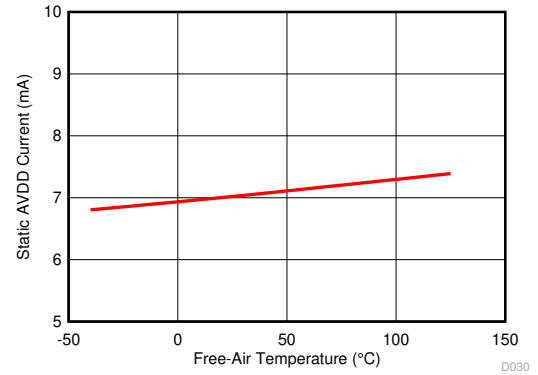
图 6-21. Dynamic AVDD Current vs Sampling Rate

6.9 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $AVDD = 5\text{ V}$, $DVDD = 3.3\text{ V}$, $V_{REFIN} = 2.5\text{ V}$, and $f_{\text{Sample}} = 2.048\text{ MSPS}$ (unless otherwise noted)



6-22. Dynamic AVDD Current vs Free-Air Temperature



6-23. Static AVDD Current vs Free-Air Temperature

7 Detailed Description

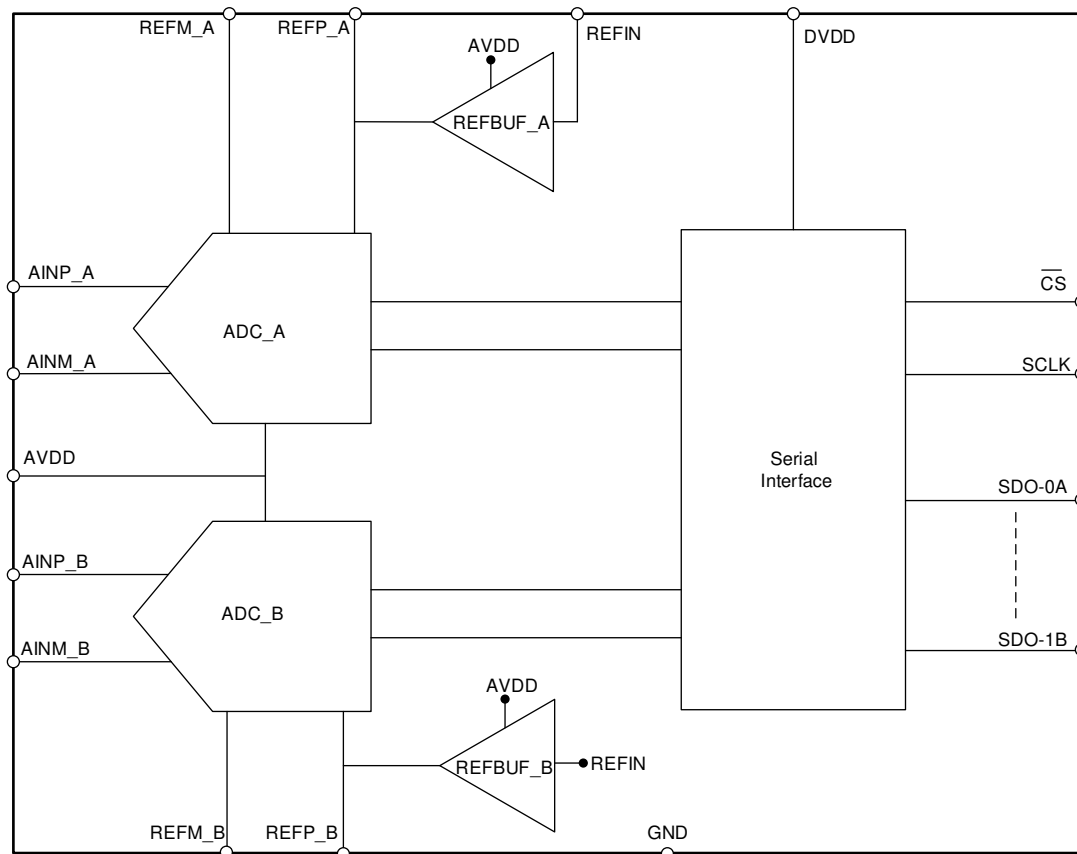
7.1 Overview

The ADS9226 is a 16-bit, dual-channel, high-speed, simultaneous-sampling, analog-to-digital converter (ADC). The device supports pseudo-differential input signals and a full-scale range equal to $2 \times V_{REFIN}$.

When a conversion is initiated, the difference between the AINP_x and AINM_x pins is sampled on the internal capacitor array. The device uses an internal clock to perform conversions. During the conversion process, both analog inputs are disconnected from the internal circuit. At the end of the conversion process, the device reconnects the sampling capacitors to the AINP_x and AINM_x pins and enters an acquisition phase. The device includes reference buffers to provide the charge required by the ADCs during conversion.

The device includes a traditional serial programming interface (SPI)-compatible serial interface to interface with a variety of microcontrollers, digital signal processors (DSPs), and field-programmable gate arrays (FPGAs).

7.2 Functional Block Diagram



7.3 Feature Description

From a functional perspective, the device is comprised of five modules: two converters (ADC_A, ADC_B), two reference buffers (REFBUF_A, REFBUF_B), and the serial interface, as illustrated in 节 7.2.

The converter module samples and converts the analog input into an equivalent digital output code. The reference buffers provide the charge required by the converters for the conversion process. The serial interface module facilitates communication and data transfer between the device and the host controller.

7.3.1 Converter Modules

As shown in 图 7-1, both converter modules sample the analog input signal (provided between the AINP_x and AINM_x pins), compare this signal with the reference voltage (between the pair of REFP_x and REFM_x pins), and generate an equivalent digital signal output code. The converter modules receive the CS input from the interface module, and output the ADCST signal and the conversion result back to the interface module.

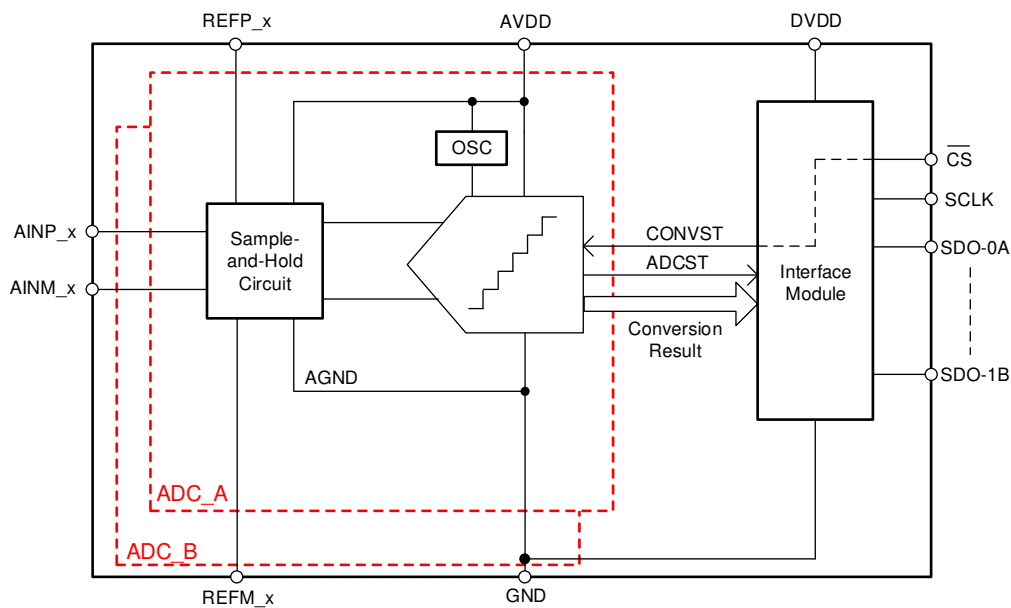


图 7-1. Converter Modules

7.3.1.1 Analog Input With Sample-and-Hold

This device supports unipolar, pseudo-differential analog input signals. 图 7-2 shows a small-signal equivalent circuit of the sample-and-hold circuit. Each sampling switch is represented by a resistance (R_{S1} and R_{S2} , typically $120\ \Omega$) in series with an ideal switch (SW_1 and SW_2). The sampling capacitors, C_{S1} and C_{S2} , are typically $16\ \text{pF}$.

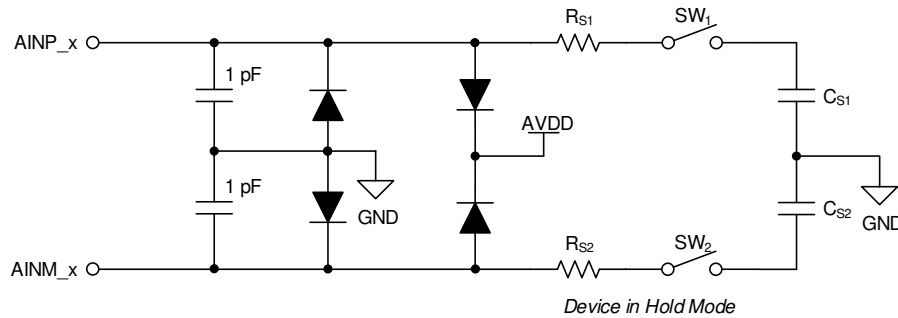


图 7-2. Analog Input Structure for Converter Module

During the acquisition process, both inputs are individually sampled on C_{S1} and C_{S2} , respectively. During the conversion process, both converters convert for the respective voltage difference between the sampled values: $V_{AINP_x} - V_{AINM_x}$.

Equation 1 and Equation 2 provide the full-scale input range (FSR) and bias voltage (V_{BIAS}) at the negative input), supported at the analog inputs for the reference voltage (V_{REFIN}) on the REFIN pin.

$$FSR = \pm V_{REFIN} = 2 \times V_{REFIN} \quad (1)$$

$$V_{BIAS} = V_{REFIN} \pm 0.1\ \text{V} \quad (2)$$

7.3.1.2 ADC Transfer Function

This device supports unipolar, pseudo-differential input signals. The device output is in two's complement format. 图 7-3 和 表 7-1 显示该器件的理想传输特性。Equation 3 给出了 ADC 的最不显著位 (LSB)。

$$1 \text{ LSB} = \text{FSR} / 2^n \tag{3}$$

where

- FSR 是在 方程式 1 中定义的
- n = 器件的分辨率

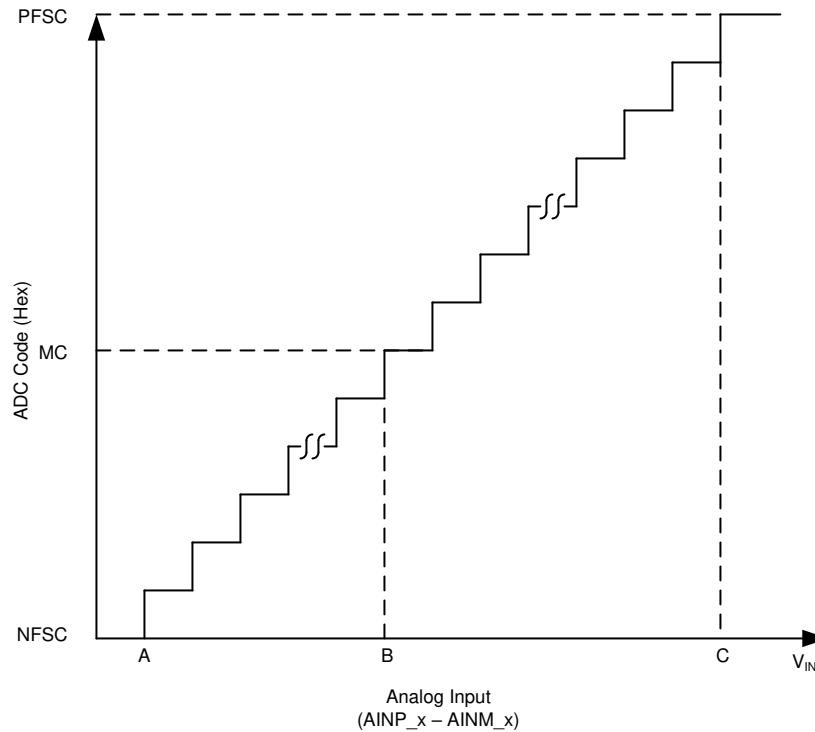


图 7-3. Ideal Transfer Characteristics

表 7-1. Transfer Characteristics

STEP	INPUT VOLTAGE (AINP_x-AINM_x)	CODE	DESCRIPTION	IDEAL OUTPUT CODE (R = 16)
A	$\leq - (V_{REF} - 0.5 \text{ LSB})$	NFSC	Negative full-scale code	8000
B	- 0.5 LSB to 0.5 LSB	MC	Mid code	0000
C	$\geq (V_{REF} - 1.5 \text{ LSB})$	PFSC	Positive full-scale code	7FFF

7.3.2 External Reference Voltage

The device requires an external reference voltage of the value V_{REFIN} , as specified in 节 6. 图 7-4 shows the connections for using the device with an external reference. A reference without an integrated buffer can be used because of the high input impedance of the REFIN pin.

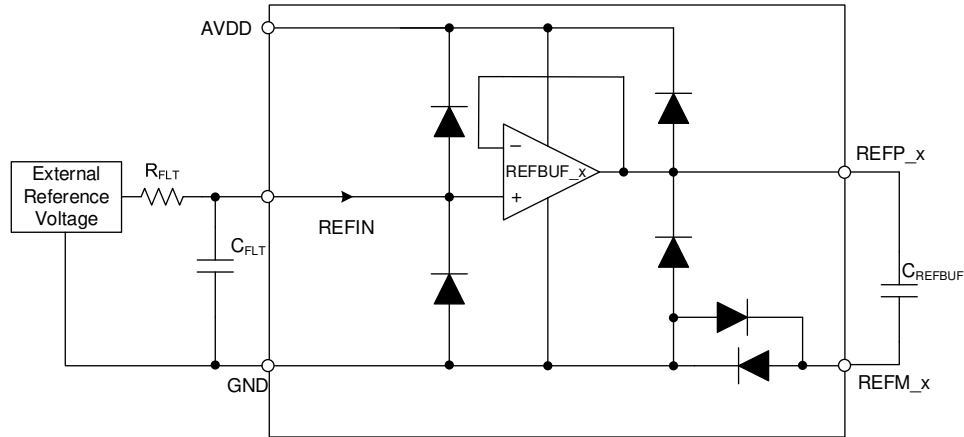


图 7-4. Connection Diagram for Reference and Reference Buffers

7.3.3 Reference Buffers

On the \overline{CS} rising edge, both converters start converting the sampled value on the analog input, and the internal capacitors are switched to the REFP_x pins. Most of the switching charge required during the conversion process is provided by the external decoupling capacitor C_{REFP_x} . If the charge lost from C_{REFP_x} is not replenished before the next \overline{CS} rising edge, the subsequent conversion occurs with this different reference voltage and causes a proportional error in the output code. To eliminate these errors, the internal reference buffers of the device maintains the voltage on the REFP_x pins.

All performance characteristics of the device are specified with the internal reference buffer and a specified value of C_{REFP_x} . As shown in 图 7-4, place a decoupling capacitor C_{REFP_x} between the REFP_x pins and the REFM_x pin as close to the device as possible.

7.4 Device Functional Modes

This device supports two functional states: acquisition phase (ACQ) and conversion phase (CNV).

7.4.1 ACQ State

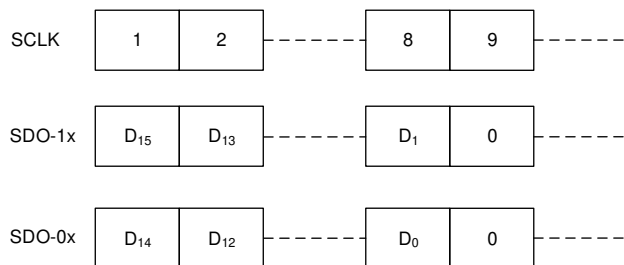
In ACQ state, the device acquires the analog input signal. The device enters ACQ state at power-up, when coming out of power down and by the ADCST signal (internal). A \overline{CS} rising edge takes the device from ACQ state to CNV state.

7.4.2 CNV State

The device moves from ACQ state to CNV state and starts conversion on a rising edge of the \overline{CS} pin. The conversion process uses an internal clock. The host must provide a minimum time of t_{CYCLE} between two subsequent start of conversions.

7.4.3 Output Data Word

The output data word consists of a conversion result of N bits where N = 16 for the ADS9226. The output data word $D[N-1:0]$, as shown in [图 7-5](#), is left-justified and split into two data lines (SDO-xy) for each ADC.



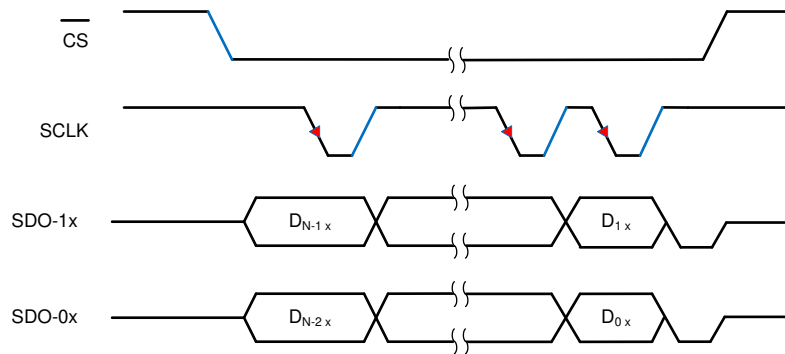
For ADC_A, x = A. For ADC_B, x = B.

图 7-5. Output Data Word

7.4.4 Conversion Control and Data Transfer Frame

A data transfer frame starts with a falling edge of the \overline{CS} signal. In any frame, the clocks provided on the SCLK pin are used to transfer the output data for the completed conversion. The device has two SDOs (SDO-0x and SDO-1x) for each ADC. For ADC_A, the device provides data on SDO-0A and SDO-1A, whereas for ADC_B, the device provides data on SDO-0B and SDO-1B. The most significant bit (D_{n-1x}) of the output data is launched on the SDO-1x pins and the MSB-1 (D_{n-2x}) bit is launched on the SDO-0x pins on the falling edge of \overline{CS} , any subsequent output bits are launched on the rising edges provided on SCLK. When all output bits of the conversion result are shifted out, the device launches 0's on the subsequent SCLK rising edges. The data transfer frame ends with a rising edge of the \overline{CS} signal. For detailed timing specifications, see [节 6](#) and [图 7-6](#).

The \overline{CS} pulse high time determines if the data being read back is with a 0 sample latency or a 1 sample latency. See [图 6-1](#) and [图 6-2](#) for the respective timing diagrams. The maximum-rated sampling rate of 2.048 MSPS is achieved with a latency-1 data capture.



For ADC_A, x = A. For ADC_B, x = B.

图 7-6. Data Transfer Frame for Reading Data

8 Application and Implementation

Note

以下应用部分的信息不属于 TI 组件规范，TI 不担保其准确性和完整性。客户应负责确定 TI 组件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

The two primary circuits required to maximize the performance of a high-precision, successive approximation register (SAR) analog-to-digital converter (ADC) are the input driver and the reference driver circuits. This section presents general principles for designing these circuits, followed by an application circuit designed using the ADS9226.

8.1.1 ADC Input Driver

The input driver circuit for a high-precision ADC mainly consists of two parts: a driving amplifier and a charge-kickback filter. The amplifier is used for signal conditioning of the input signal and the low output impedance of the amplifier provides a buffer between the signal source and the switched-capacitor inputs of the ADC. The charge-kickback filter helps attenuate the sampling charge injection from the switched-capacitor input stage of the ADC, and band-limits the wideband noise contributed by the front-end circuit. Careful design of the front-end circuit is critical to meet the linearity and noise performance of the ADS9226.

8.1.1.1 Charge-Kickback Filter

The charge-kickback filter is an RC filter at the input pins of the ADC that filters the broadband noise from the front-end drive circuitry and attenuates the sampling charge injection from the switched-capacitor input stage of the ADC. A filter capacitor, C_{FLT} (as shown in 图 8-1), is connected from each input pin of the ADC to ground. This capacitor helps reduce the sampling charge injection and provides a charge bucket to quickly charge the internal sample-and-hold capacitors during the acquisition process. Generally, the value of this capacitor must be at least 20 times the specified value of the ADC sampling capacitance. For the ADS9226, the input sampling capacitance is equal to 16 pF; therefore, for optimal performance, keep C_{FLT} greater than 320 pF. This capacitor must be a COG- or NPO-type. The type of dielectric used in COG or NPO ceramic capacitors provides the most stable electrical properties over voltage, frequency, and temperature changes.

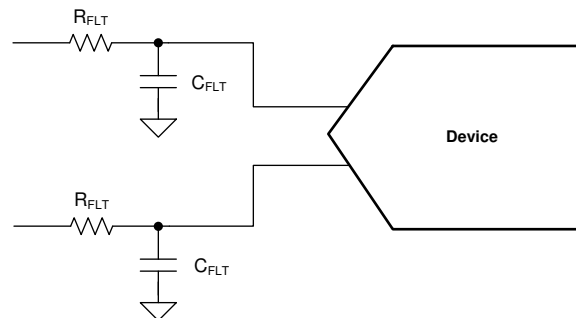


图 8-1. Charge-Kickback Filter

Driving capacitive loads can degrade the phase margin of the input amplifier, thus making the amplifier marginally unstable. To avoid amplifier stability issues, series isolation resistors (R_{FLT}) are used at the output of the amplifiers. A higher value of R_{FLT} helps with amplifier stability, but adds distortion as a result of interactions with the nonlinear input impedance of the ADC. Distortion increases with source impedance, input signal frequency, and input signal amplitude. Therefore, the selection of R_{FLT} requires balancing the stability of the driver amplifier and distortion performance of the design. Always verify the stability and settling behavior of the driving amplifier and charge-kickback filter by TINA-TI™ SPICE simulation. Keep the tolerance of the selected resistors less than 1% to keep the inputs balanced.

8.1.2 Input Amplifier Selection

Selection criteria for the input amplifiers is highly dependent on the input signal type, as well as the performance goals, of the data acquisition system. Some key amplifier specifications to consider when selecting an appropriate amplifier to drive the inputs of the ADC are:

- Small-signal bandwidth. Select the small-signal bandwidth of the input amplifiers to be as high as possible after meeting the power budget of the system. Higher bandwidth reduces the closed-loop output impedance of the amplifier, thus allowing the amplifier to more easily drive the ADC sample-and-hold capacitor and the RC filter (the charge-kickback filter) at the inputs of the ADC. Higher bandwidth amplifiers offer faster settling times when driving the capacitive load of the charge-kickback filter, thus reducing harmonic distortion at higher input frequencies. Equation 4 describes the unity-gain bandwidth (UGB) of the amplifier to be selected in order to maintain the overall stability of the input driver circuit:

$$UGB \geq 4 \times \left(\frac{1}{2\pi \times R_{FLT} \times C_{FLT}} \right) \quad (4)$$

- Distortion. Both the ADC and the input driver introduce distortion in a data acquisition block. Equation 5 shows that to make sure that the distortion performance of the data acquisition system is not limited by the front-end circuit, the distortion of the input driver must be at least 10 dB less than the distortion of the ADC:

$$THD_{AMP} \leq THD_{ADC} - 10 \text{ (dB)} \quad (5)$$

- Noise. Noise contribution of the front-end amplifiers must be as low as possible to prevent any degradation in SNR performance of the system. Generally, to make sure that the noise performance of the data acquisition system is not limited by the front-end circuit, the total noise contribution from the front-end circuit must be kept below 20% of the input-referred noise of the ADC. Equation 6 explains that noise from the input driver circuit is band-limited by designing a low cutoff frequency, charge-kickback filter:

$$N_G \times \sqrt{2} \times \sqrt{\left(\frac{V_{1/f_AMP_PP}}{6.6} \right)^2 + e_{n_RMS}^2 \times \frac{\pi}{2} \times f_{-3dB}} \leq \frac{1}{5} \times \frac{V_{REF}}{\sqrt{2}} \times 10^{\left(\frac{SNR(dB)}{20} \right)} \quad (6)$$

where

- V_{1/f_AMP_PP} is the peak-to-peak flicker noise in μV
- e_{n_RMS} is the amplifier broadband noise density in nV/\sqrt{Hz}
- f_{-3dB} is the 3-dB bandwidth of the charge-kickback filter
- N_G is the noise gain of the front-end circuit that is equal to 1 in a buffer configuration
- Settling Time. For DC signals with fast transients that are common in a multiplexed application, the input signal must settle within an 16-bit accuracy at the device inputs during the acquisition time window. This condition is critical to maintain the overall linearity performance of the ADC. Settling accuracy for DC transients directly translates to the linear performance for AC input signals, especially those that may use the ADC full-scale range. Typically, amplifier data sheets specify the output settling performance only up to 0.1% to 0.001%, which may not be sufficient for the desired 16-bit accuracy. Therefore, always verify the settling behavior of the input driver by TINA-TI SPICE simulations before selecting the amplifier.

8.2 Typical Application

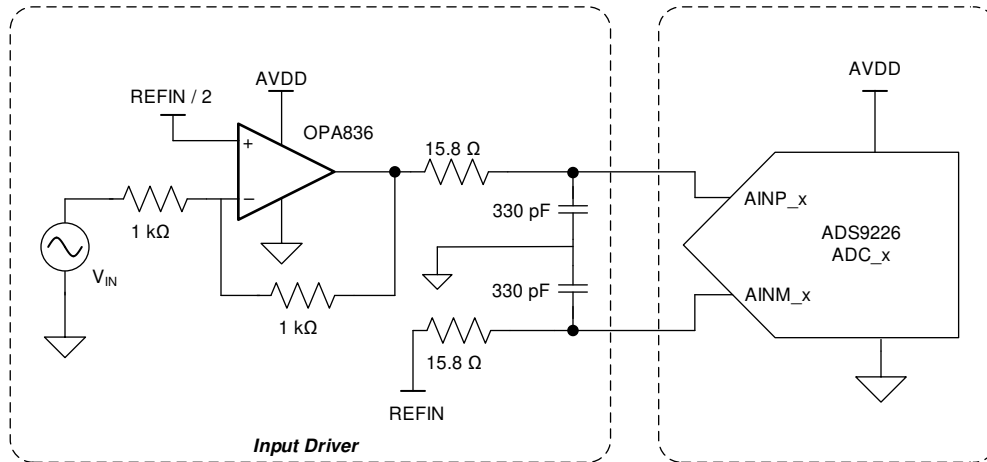


图 8-2. Typical Connection Diagram of the ADS9226 Application Circuit

8.2.1 Design Requirements

The design parameters are listed in 表 8-1 for this example.

表 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
ADC sample rate	2 MSPS
Analog input signal	2 kHz, ± 2.5 V, pseudo-differential
SNR	> 87 dB
THD	< - 100 dB
Power supply	5-V analog, 3.3-V digital

8.2.2 Detailed Design Procedure

图 8-2 shows an application circuit for this example. The device incorporates two independently matched reference buffers for each ADC. Decouple the reference buffer outputs (the REFP_A and REFP_B pins) with the REFM_A and REFM_B pins, respectively, with 10- μ F decoupling capacitors. The circuit in 图 8-2 shows a pseudo-differential data acquisition (DAQ) block optimized for low distortion and noise using the OPA836 and the ADS9226. The single-ended inputs are level-shifted and driven using a high-bandwidth, low-distortion, operational amplifier configured with a gain of -1 V/V and an optimal RC charge-kickback filter before going to the ADC. Generally, the distortion from the input driver must be at least 10 dB less than the ADC distortion. Therefore, these circuits use the OPA836 as an input driver that provides exceptional AC performance because of its extremely low-distortion and high bandwidth specifications. In addition, the components of the charge-kickback filter are selected to keep the noise from the front-end circuit low without adding distortion.

8.2.3 Application Curve

图 8-3 provides the typical FFT for the circuit shown in 图 8-2.

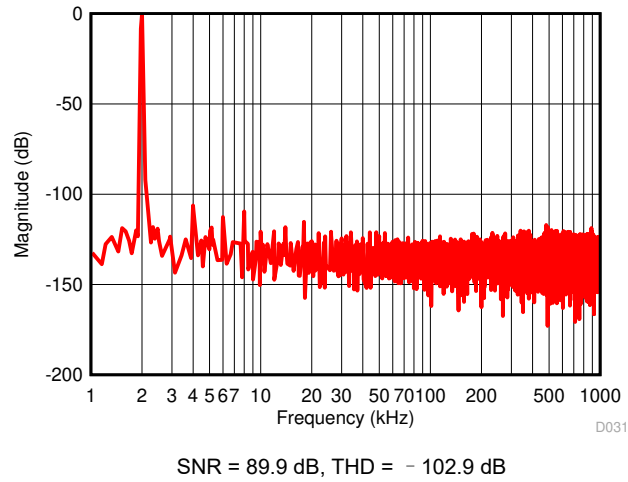


图 8-3. Typical FFT With a 2-kHz Signal

9 Power Supply Recommendations

The device has two separate power supplies: AVDD and DVDD. The reference buffers and converter modules (ADC_A and ADC_B) operate on AVDD. The serial interface operates on DVDD. AVDD and DVDD can be independently set to any value within their permissible ranges.

As shown in [图 9-1](#), connect pins 12 and 29 together and place 1- μ F decoupling capacitors between pin 12 (AVDD) and pin 11 (GND), and between pin 29 (AVDD) and pin 30 (GND). To decouple the DVDD supply, place a 1- μ F decoupling capacitor between pin 28 (DVDD) and pin 27 (GND), and between pin 26 (DVDD) and pin 27 (GND).

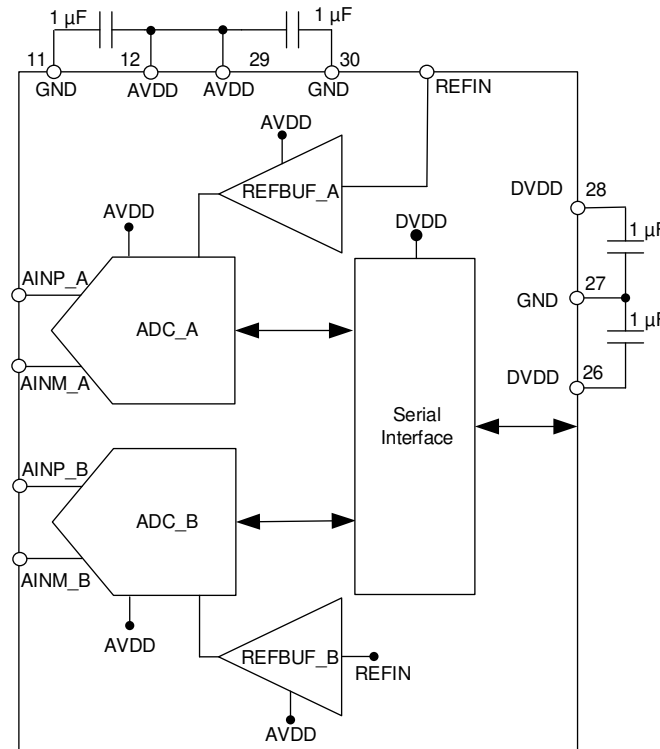


图 9-1. Power-Supply Decoupling

10 Layout

10.1 Layout Guidelines

This section provides some layout guidelines for achieving optimum performance with the ADS9226.

10.1.1 Signal Path

Route the analog input signals in opposite directions to the digital connections. The reference decoupling components are kept away from the switching digital signals. This arrangement prevents noise generated by digital switching activity from coupling to sensitive analog signals.

10.1.2 Grounding and PCB Stack-Up

Low inductance grounding is critical for achieving optimum performance. Grounding inductance is kept below 1 nH with 15-mil grounding vias and a printed circuit board (PCB) layout design that has at least four layers. Place all critical components of the signal chain on the top layer with a solid analog ground from subsequent inner layers to minimize via length to ground.

10.1.3 Decoupling of Power Supplies

Place the decoupling capacitors on AVDD and DVDD within 20 mil from the respective pins, and use a 15-mil via to ground from each capacitor. Avoid placing vias between any supply pin and the respective decoupling capacitor.

10.1.4 Reference Decoupling

Dynamic currents are present at the REFP_x and REFM_x pins during the conversion phase, and excellent decoupling is required to achieve optimum performance. Place a 10- μ F, X7R-grade, ceramic capacitor with at least a 10-V rating. Select 0603- or 0805-size capacitors to keep equivalent series inductance (ESL) low. Connect the REFM_x pins to the decoupling capacitor before a ground via. Also place decoupling capacitors on the REFby2 pin.

10.1.5 Analog Input Decoupling

Dynamic currents are also present at the pseudo-differential analog inputs of the ADS9226. Use C0G- or NPO-type capacitors to decouple these inputs because with these types of capacitors, capacitance stays almost constant over the full input voltage range. Lower-quality capacitors (such as X5R and X7R) have large capacitance changes over the full input-voltage range that may cause degradation in the performance of the device.

10.2 Layout Example

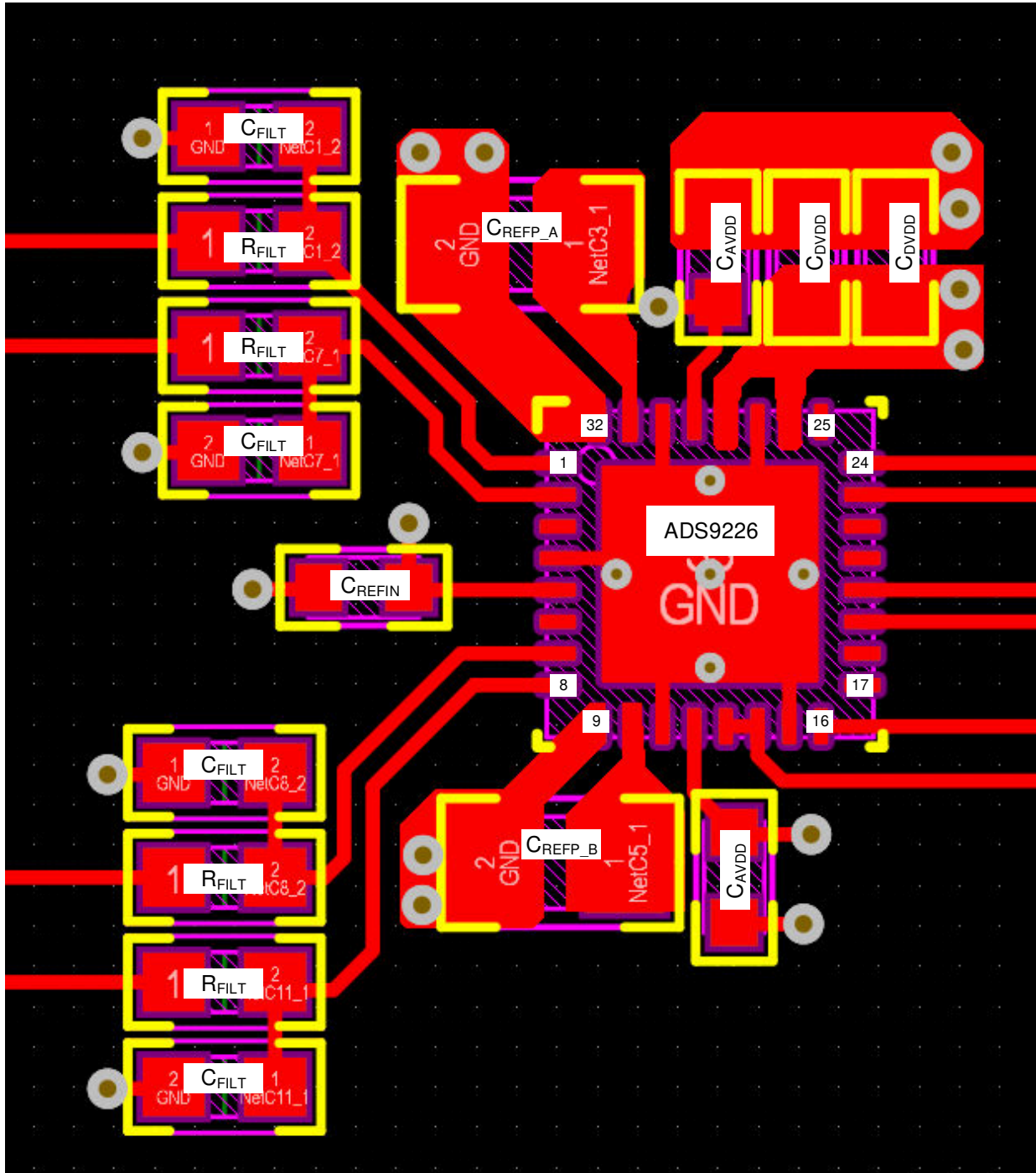


图 10-1. Example Layout for the ADS9226

11 Device and Documentation Support

11.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [REF50xx Low-Noise, Very Low Drift, Precision Voltage Reference data sheet](#)
- Texas Instruments, [OPAx836 Very Low Power, Rail-ro-Rail Out Operational Amplifiers data sheet](#)

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ADS9226IRHBR	ACTIVE	VQFN	RHB	32	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	ADS9226	Samples
ADS9226IRHBT	ACTIVE	VQFN	RHB	32	250	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	ADS9226	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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GENERIC PACKAGE VIEW

RHB 32

VQFN - 1 mm max height

5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224745/A



4223442/B 08/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

RHB0032E

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
SCALE:18X



SOLDER MASK DETAILS

4223442/B 08/2019

NOTES: (continued)

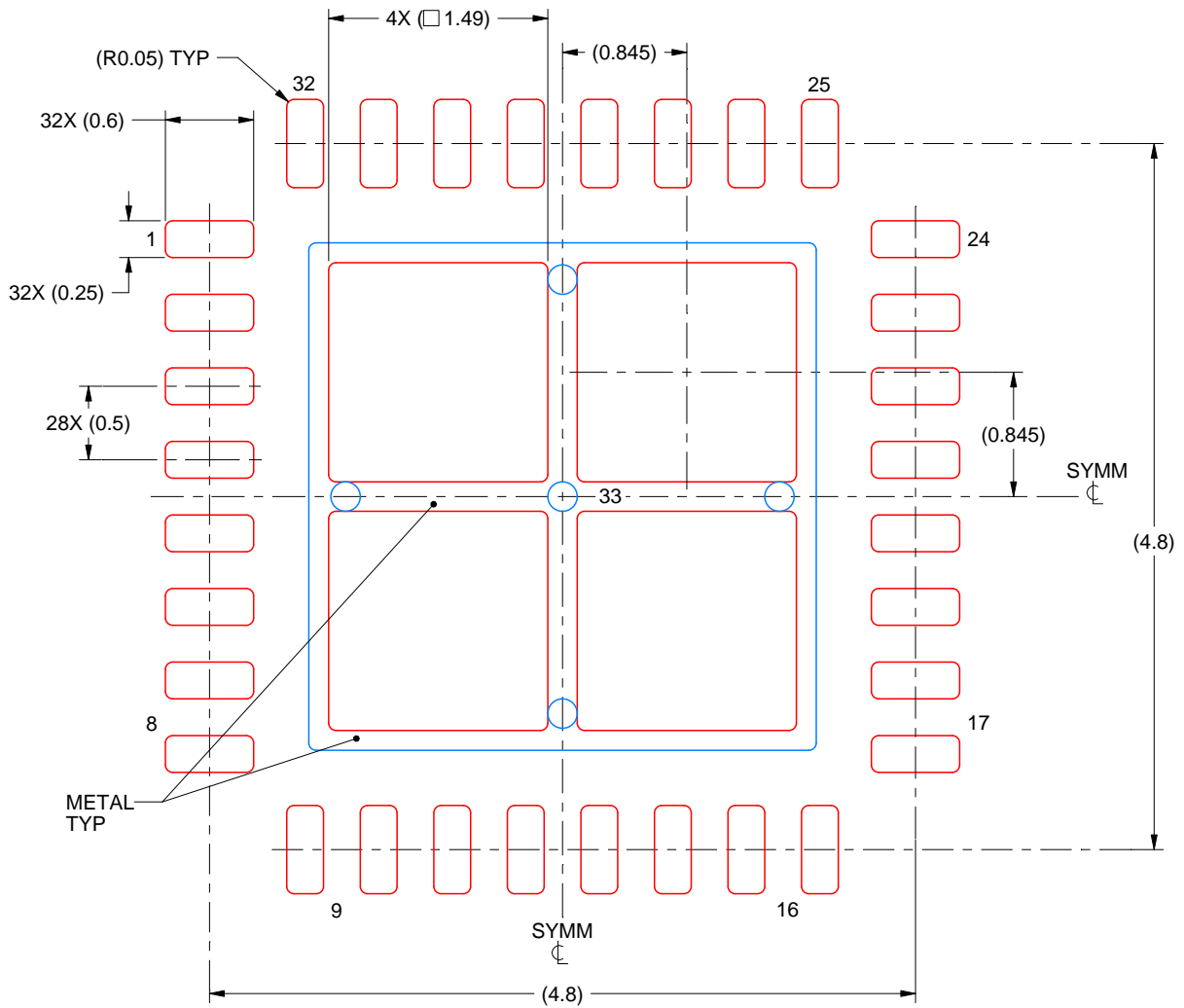
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RHB0032E

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 33:
 75% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
 SCALE:20X

4223442/B 08/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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